



*Simulation of 3D InGaN/GaN MQW  
LED with textured surface*

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**CROSLIGHT**  
Software Inc.

# Introduction

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**Step1:**

**3D structure built by Csuprem**

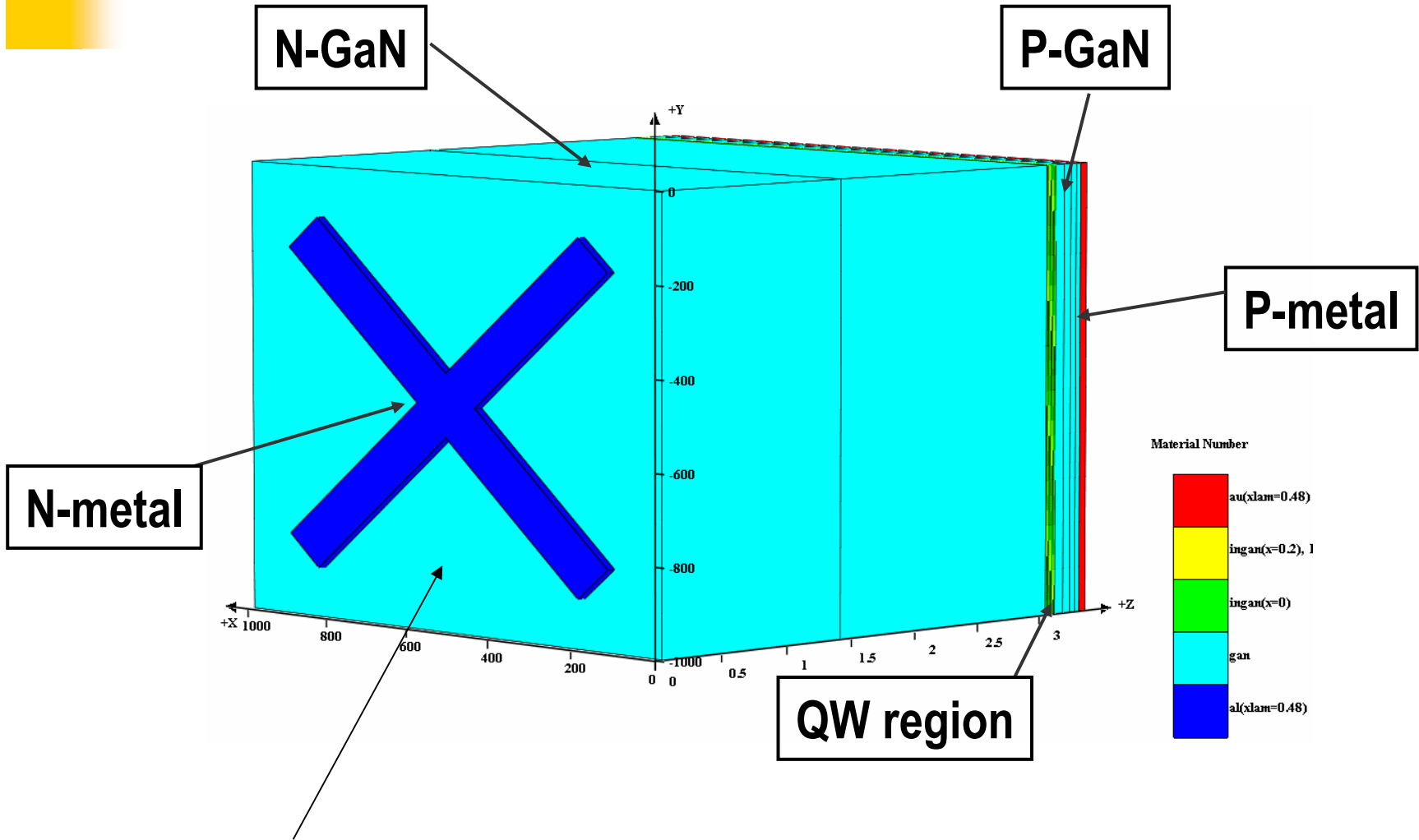
**Step2:**

**Texture modeling by Apsys and FDTD**

**Step3:**

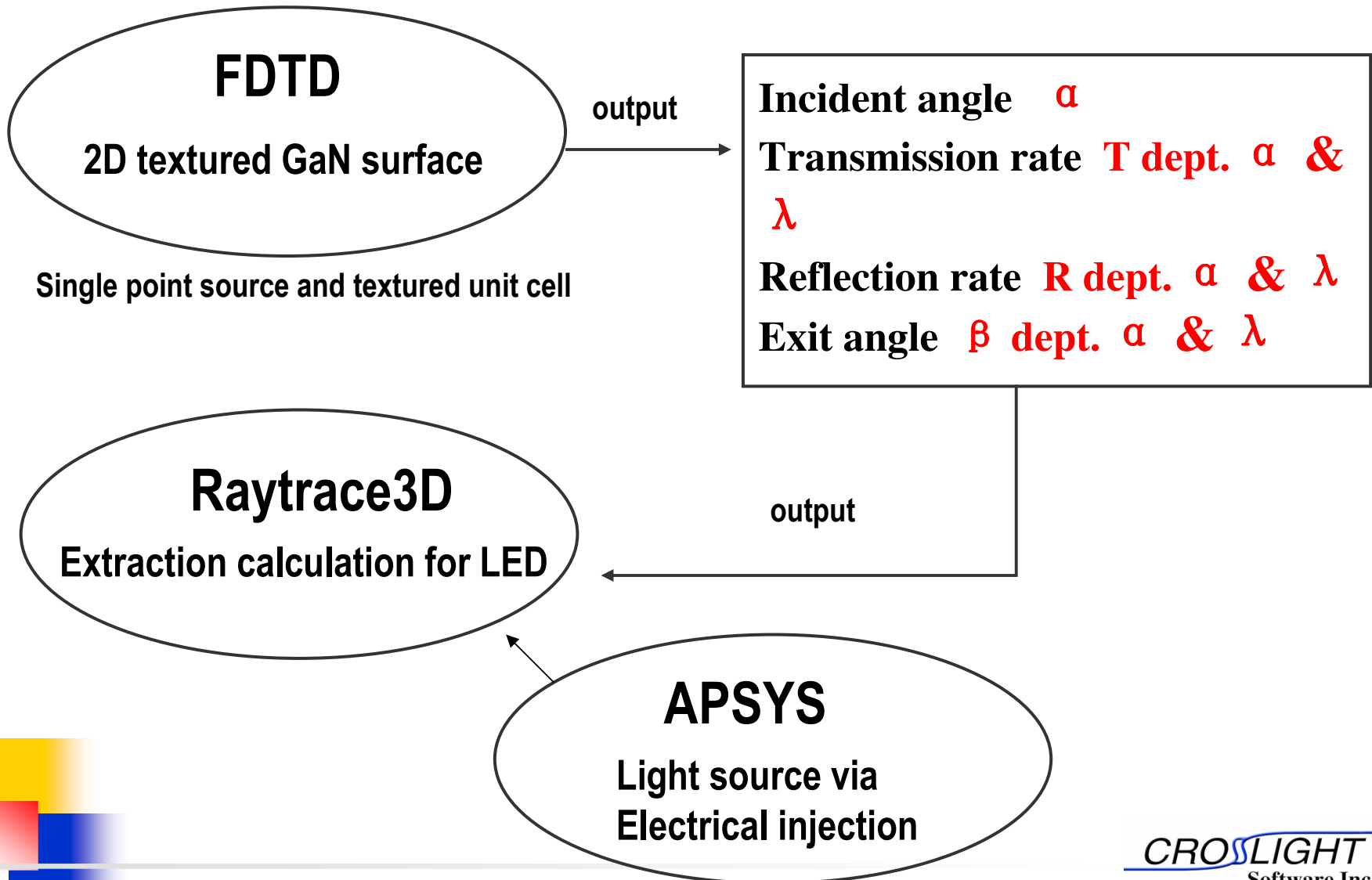
**Calculation of electrical and optical properties by Apsys and Raytrace-3D (RT3D)**

# 3D structure



Assume N-type GaN surface is textured

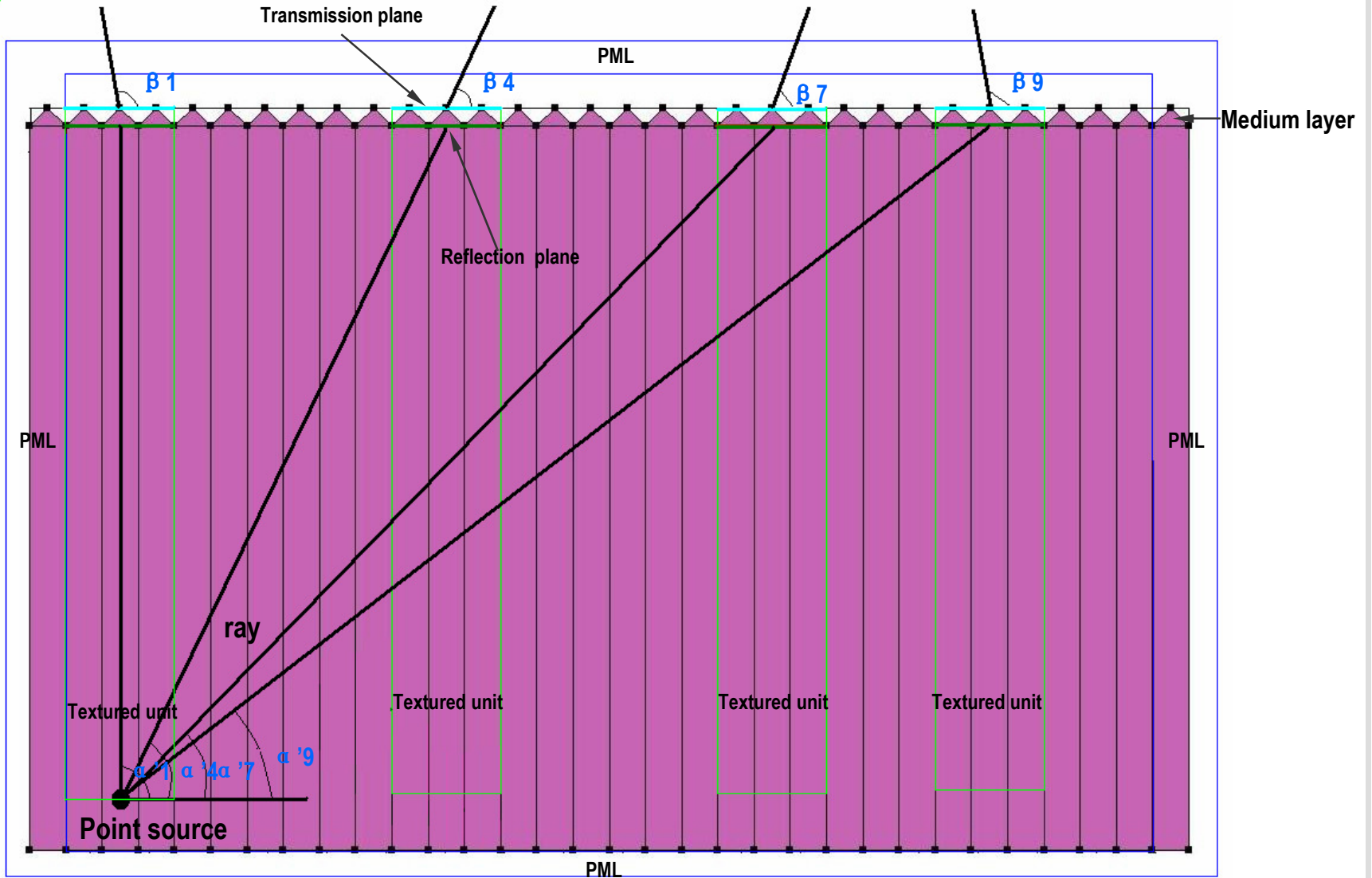
# Texture modeling



# **Texture modeling by FDTD**

- 1. Setup a portion of LED surface suitable for FDTD.**
- 2. Set a single point source at a proper distance from textured surface.**
- 3. Division of texture units into blocks to extract transmission/reflection coefficient as a function of incident angles.**
- 4. Calculate the far field distribution of optical energy from each block to extract the average emission angle.**

# Texture modeling



FDTD Cell (33 x 23.5  $\mu\text{m}$ )

# RT3D simulation with FDTD data

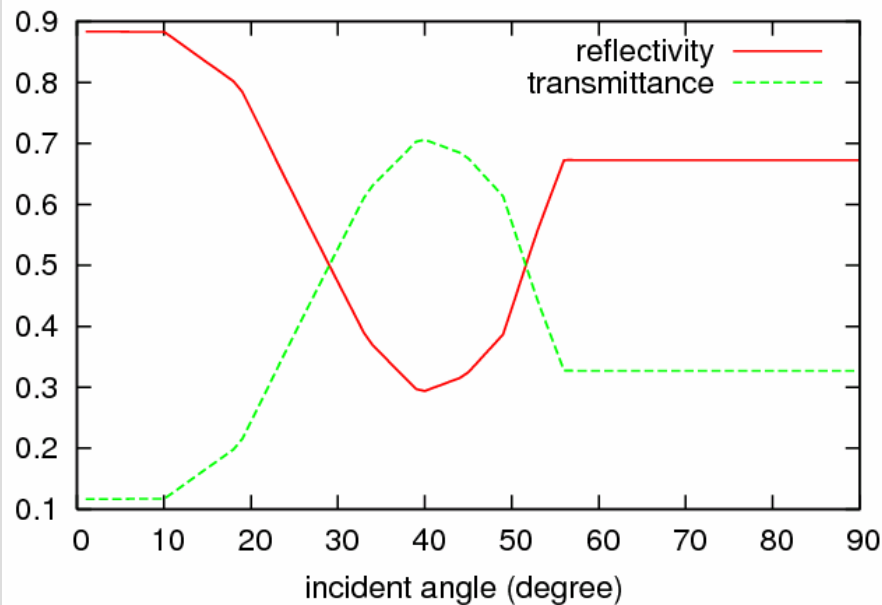
**Note:**

The textured surface is treated as a special boundary in RT3D simulation, which means that at this special boundary, reflection, transmission will not be calculated according to Fresnel equations for geometrical optics, but be calculated according to data extracted from FDTD.

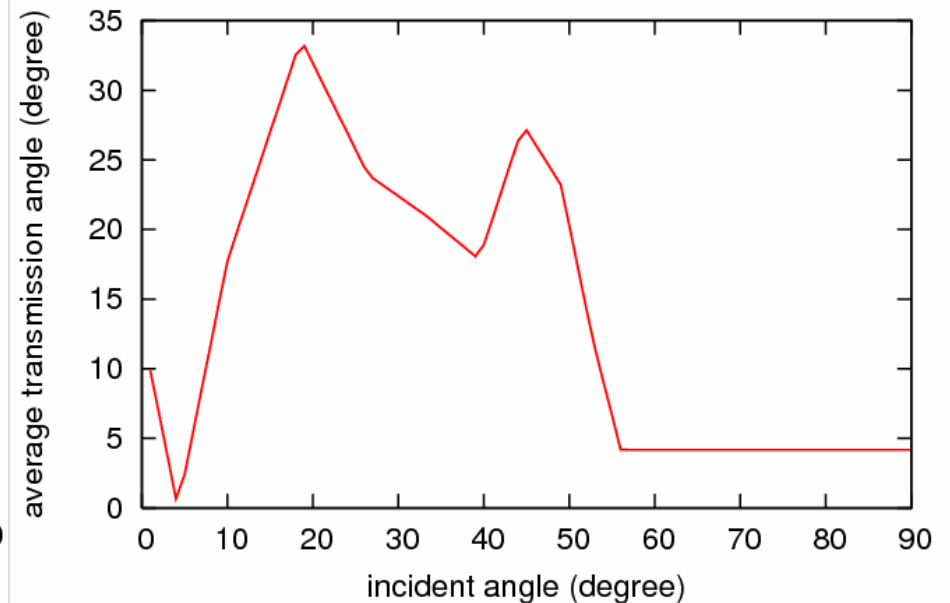
# RT3D simulation with FDTD data

Data extracted from FDTD

Reflectivity and Transmittance versus incident angle



Average transmission angle versus incident angle

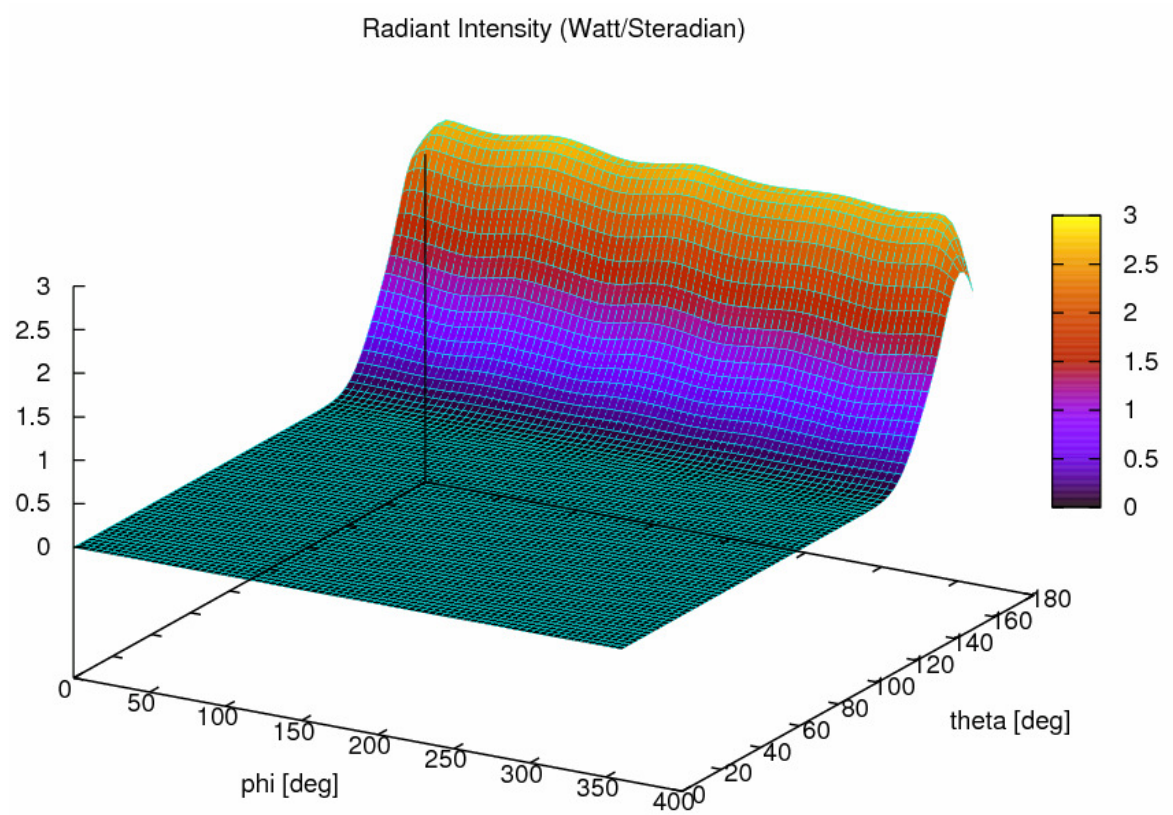




# Raytracing using FDTD data

Result: power distribution

Result shows that output is mainly outwards from the textured surface ( - Z direction).



Power distribution in spherical coordinates

# RT3D simulation with FDTD data

## Result: power extraction efficiency

Total source power (W)

4.78620413176667

TRANSMITTED POWER in absolute and relative to emitted (%) units

0.6969

14.56

SEMICONDUCTOR ABSORBED POWER in absolute and relative to emitted (%) units

4.0893

85.44

Total source power (W)

4.78620413176667

TRANSMITTED POWER in absolute and relative to emitted (%) units

3.735

78.03

SEMICONDUCTOR ABSORBED POWER in absolute and relative to emitted (%) units

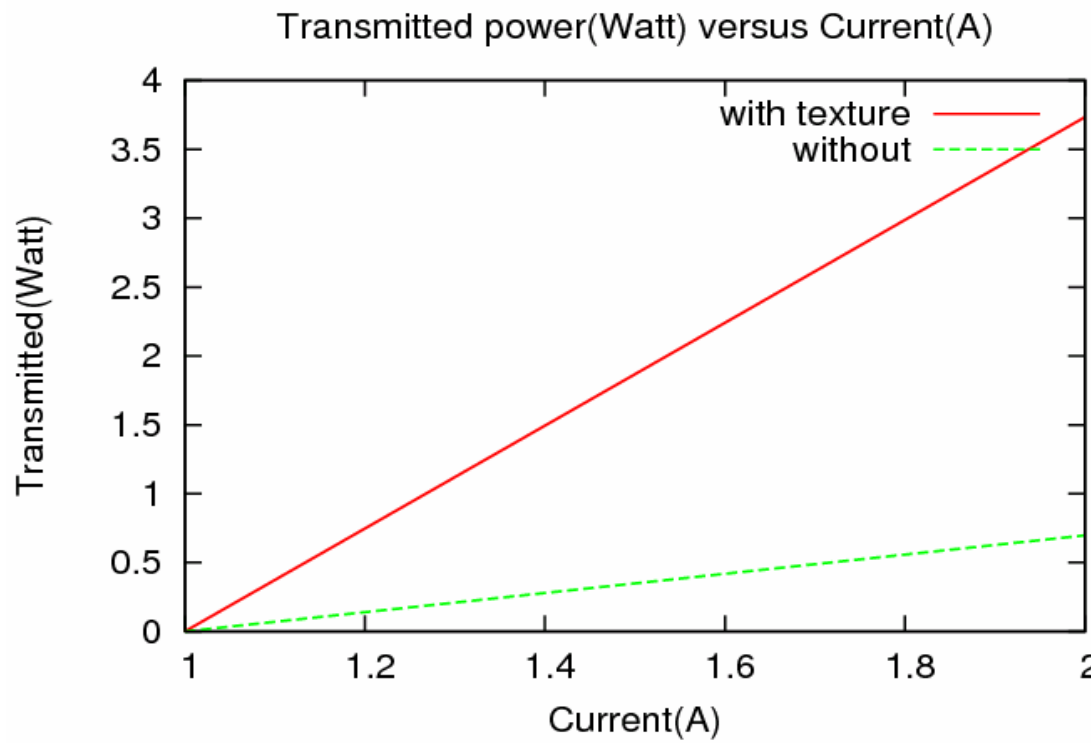
1.052

21.97

Results shows that power extraction efficiency is much enhanced .

# RT3D simulation with FDTD data

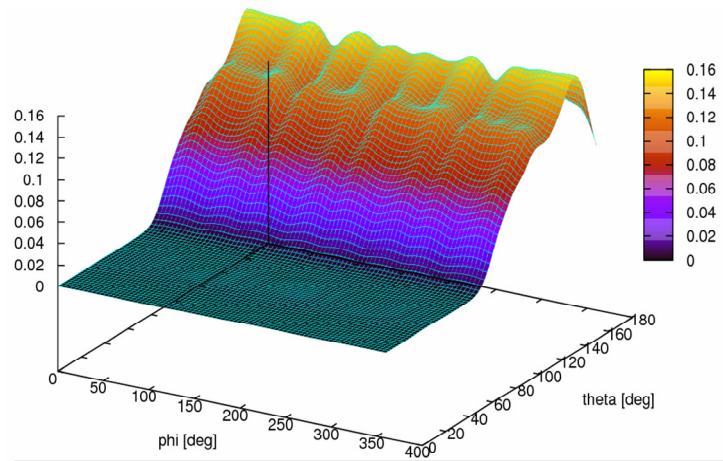
Compare: power extraction



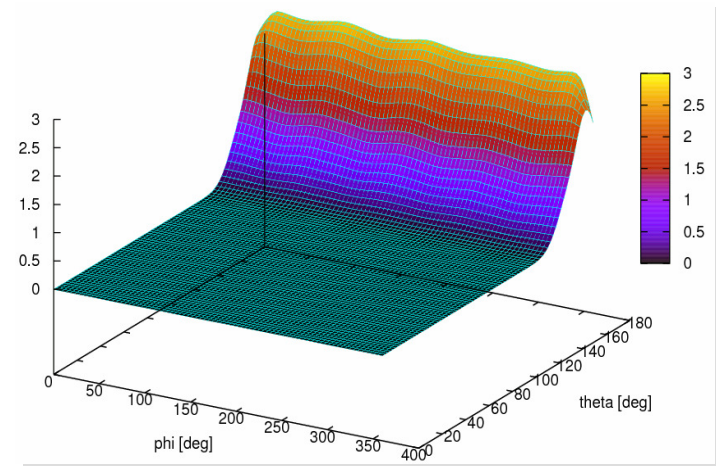
Result shows emission power enhanced by a factor of five or more.

# RT3D simulation with FDTD data

Compare: power distribution



Transmitted light power distribution  
without textured surface

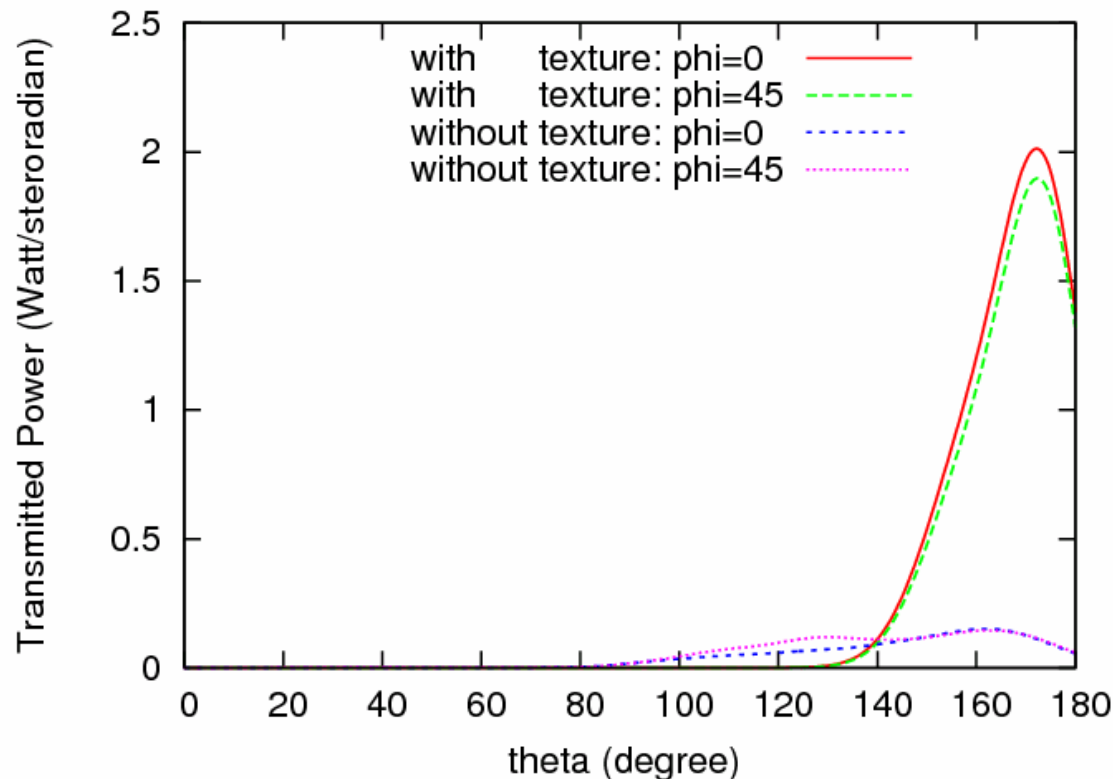


Transmitted light power distribution  
with textured surface

More uniform angular distribution obtained with texture.

# RT3D simulation with FDTD data

## Compare: power distribution



- theta dependence for transmitted power at phi=0,45 degrees.
- It indicates power emission is nearly symmetric with respect to phi angle.

## Summary

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**Accurate simulation of textured light emitting diode achieved through integration of several modules of Crosslight Software.**

**CSuprem+Apsys provide the basic device structure and electrical injection modeling.**

**FDTD+Raytrace-3D provide the optical power extraction simulation.**